

Xiaojuan LIU, Guomei WANG, Mingxiao ZHU, Kezhen HAN, Wenfei ZHANG, Huanian ZHANG, 2021. Traditional soliton erbium-doped fiber laser with InSe as saturable absorber. *Frontiers of Information Technology & Electronic Engineering*, 22(3):325-333. <https://doi.org/10.1631/FITEE.2000387>

# Traditional soliton erbium-doped fiber laser with InSe as saturable absorber

**Key words:** Fiber Laser; Nanosheets; Traditional soliton

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# Motivation

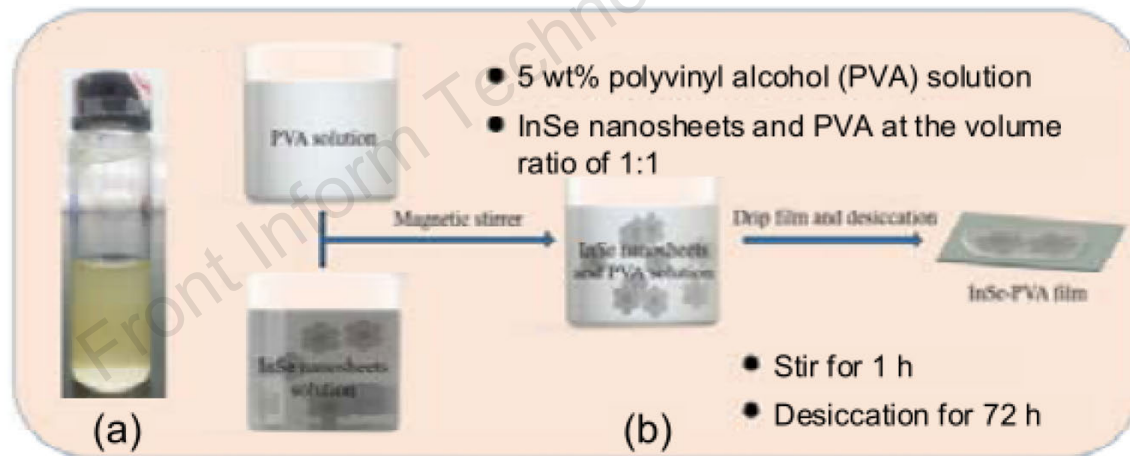
1. Two-dimensional (2D) materials exhibit distinct properties compared with traditional materials, such as high damage threshold, fast response recovery, and excellent nonlinear absorption.
2. The pulsed fiber laser, which has been widely used in the fields of industrial manufacturing and biomedicine, and in scientific research, is typically applied in the field of 2D materials.

# Main idea

InSe is a typical III-V group metal-chalcogenide compound, showing four covalently bonded Se-In-In-Se atomic planes. The adjacent layers are bonded through van der Waals interactions. The nanosheets can be prepared by mechanical exfoliation or the liquid phase exfoliation (LPE) method.

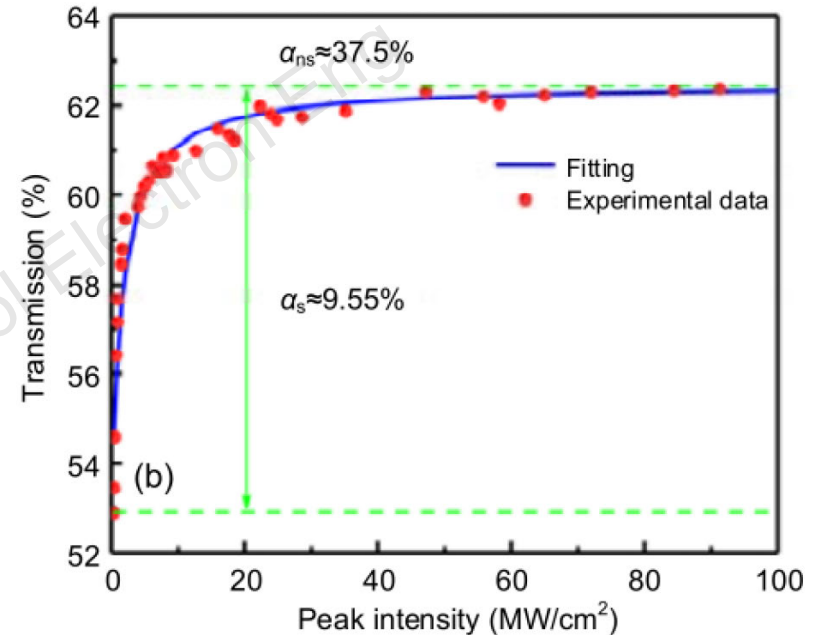
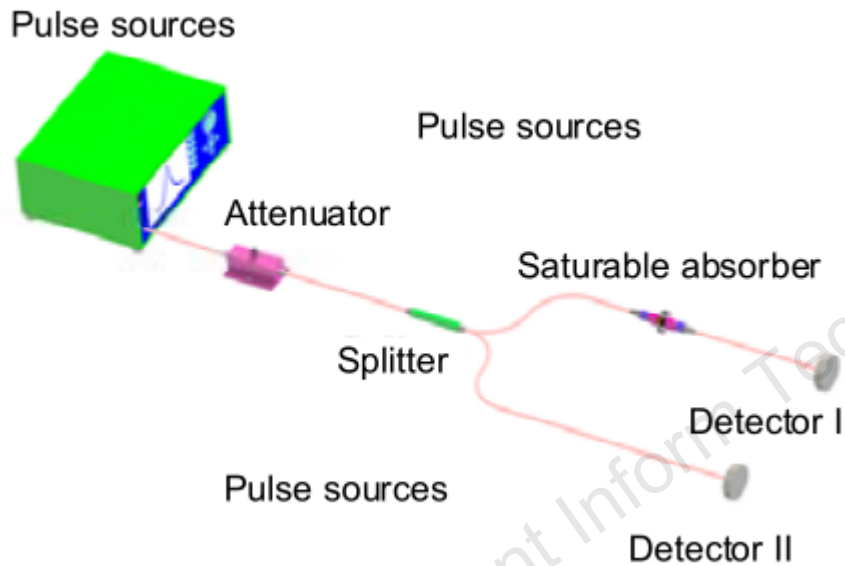
# Method

1. The dispersion solution of InSe nanosheets is purchased (Haolai Tech., China) (Fig. 1a).
2. The procedure for the fabrication of InSe-SA is shown in Fig. 1b.



**Fig. 1** The image of commercial InSe nanosheets dispersion solution (a) and the procedure for the fabrication of InSe-SA (b)

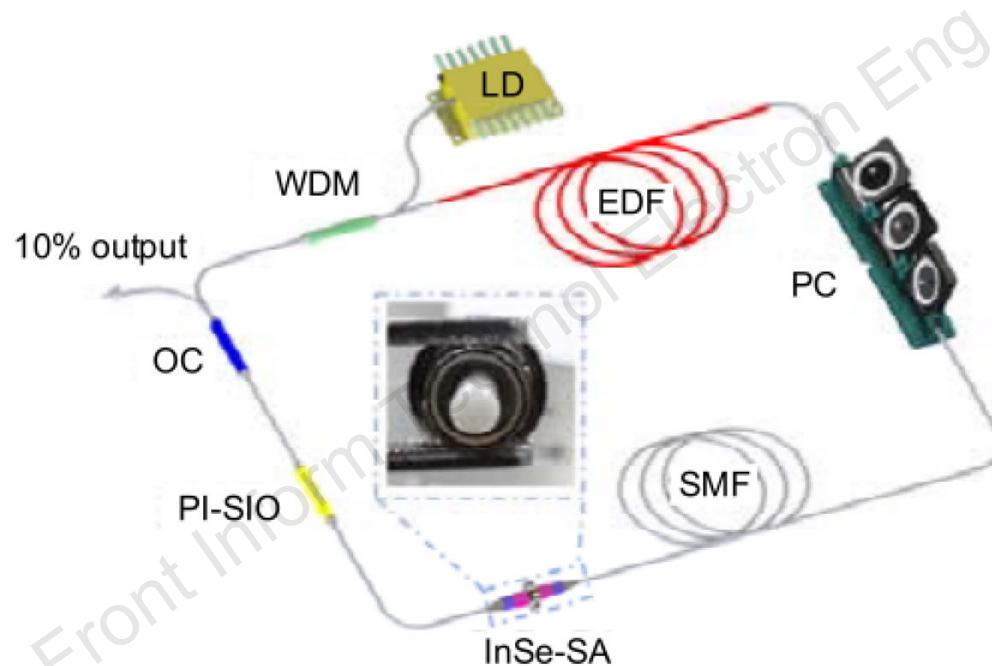
# Method



**Setup for measuring the saturable absorption properties**

**Measured and fitted nonlinear absorption properties of InSe-SA. The nonsaturable absorption and modulation depth are 37.5% and 9.55%, respectively.**

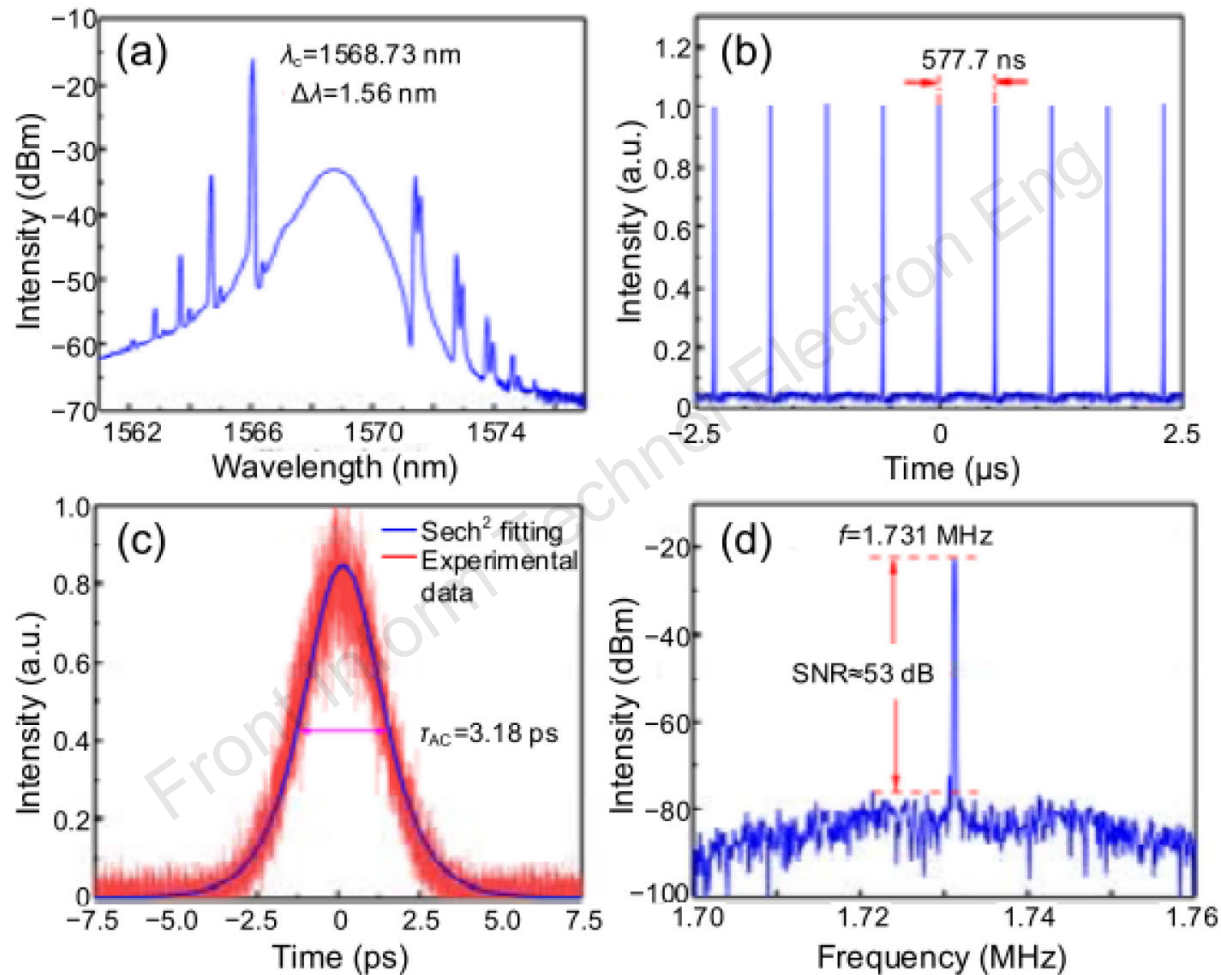
# Experimental setup



**Fig. 4 Schematic of fiber laser setup**

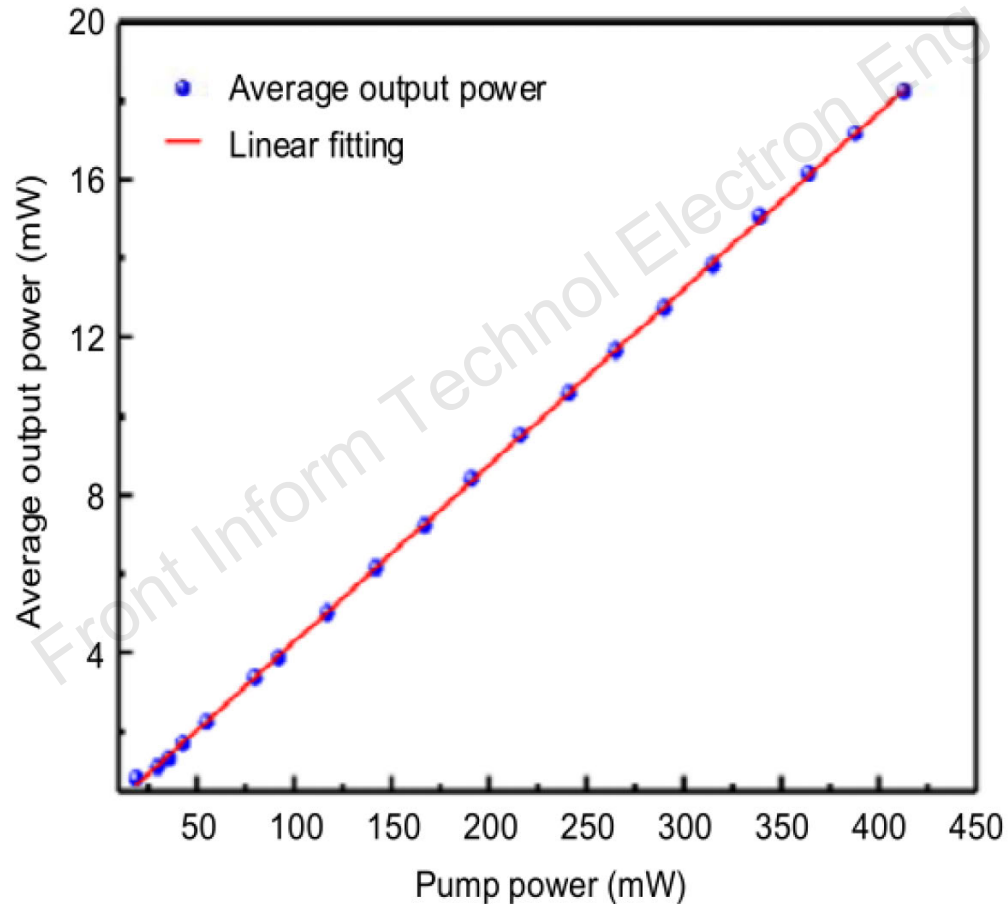
LD: laser diode; WDM: wavelength division multiplexer; EDF: erbium-doped fiber; PC: polarization controller; SMF: single-mode fiber; SA: saturable absorber; PI-ISO: polarization-independent isolator; OC: optical coupler

# Major results



**Fig. 5** Characteristics of mode-locked operation: (a) the spectrum with 3-dB bandwidth of 1.56 nm centered at 1568.73 nm; (b) the pulse interval of 577.7 ns between adjacent pulses; (c) autocorrelation trace for an output pulse with sech2 fit and the FWHM being 3.18 ps; (d) the RF spectrum with a fundamental repetition rate of 1.731 MHz and the SNR greater than 53 dB

# Major results (Cont'd)



**Fig. 7** The evolution of the average output power with the increase of the pump power

# Major results

**Table 1 Comparison of different In<sub>2</sub>Se<sub>3</sub> or InSe based SA fiber lasers**

Material	Material fabrication	SA fabrication	Modulation depth (%)	Operation	Central wave-length (nm)	Pulse duration	Reference
In <sub>2</sub> Se <sub>3</sub>	Mechanical exfoliation	Sandwiched	14.6	Mode-locked	1503.8	5.79 ps	Ahmad et al. (2018a)
In <sub>2</sub> Se <sub>3</sub>	Mechanical exfoliation	Sandwiched	22.48	Q-switched	Tunable	Tunable	Ahmad et al. (2018b)
In <sub>2</sub> Se <sub>3</sub>	Magnetron-sputtering deposition	Microfiber	4.5	TS	1565	276 fs	Yan et al. (2018)
			6.9	TS	1932	1.02 ps	
In <sub>2</sub> Se <sub>3</sub>	LPE	Sandwiched	14	TS	Switchable	1.88/1.76 ps	Wang GM et al. (2019)
InSe	LPE	Microfiber	3.4	Q-switched	Tunable	Tunable	Xu NN et al. (2018)
InSe	LPE	Sandwiched	4.2	Mode-locked	1068.36	1.37 ns	Xu NN et al. (2018)
InSe	LPE	Sandwiched	16.5	Mode-locked	–	389.2 ns	Fu et al. (2019)
InSe	LPE	Sandwiched	9.55	TS	1568.73	2.06 ps	This work

SA: saturable absorber; LPE: liquid phase exfoliation; TS: traditional soliton

# Conclusions

1. The InSe-SA was obtained with the nonsaturable absorption and modulation depth being 37.5% and 9.55%, respectively.
2. The traditional soliton was obtained for the first time with InSe as the saturable absorber, whose central wavelength, pulse width, and repetition rate are 1568.73 nm, 2.06 ps, and 1.731 MHz, respectively.
3. The study further shows that InSe is a promising material for developing ultrafast optoelectronics devices.